

2N6557
2N6558
2N6559

**NPN SILICON
HIGH VOLTAGE TRANSISTOR**



TO-202 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N6557 series types are NPN silicon, triple diffused transistors designed for video output and similar applications where high breakdown voltage is required.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Collector-Base Voltage	V_{CB0}	250	300	350	V
Collector-Emitter Voltage	V_{CEO}	250	300	350	V
Emitter-Base Voltage	V_{EBO}		6.0		V
Continuous Collector Current	I_C		0.5		A
Peak Collector Current	I_{CM}		0.7		A
Continuous Base Current	I_B		0.25		A
Power Dissipation	P_D		2.0		W
Power Dissipation ($T_C=25^\circ\text{C}$)	P_D		10		W
Operating and Storage Junction Temperature	T_J, T_{stg}		-65 to +150		$^\circ\text{C}$
Thermal Resistance	θ_{JA}		62.5		$^\circ\text{C/W}$
Thermal Resistance	θ_{JC}		12.5		$^\circ\text{C/W}$

SYMBOL	2N6557	2N6558	2N6559	UNITS
V_{CB0}	250	300	350	V
V_{CEO}	250	300	350	V
V_{EBO}		6.0		V
I_C		0.5		A
I_{CM}		0.7		A
I_B		0.25		A
P_D		2.0		W
P_D		10		W
T_J, T_{stg}		-65 to +150		$^\circ\text{C}$
θ_{JA}		62.5		$^\circ\text{C/W}$
θ_{JC}		12.5		$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	2N6557		2N6558		2N6559		UNITS
		MIN	MAX	MIN	MAX	MIN	MAX	
I_{CBO}	$V_{CB}=150\text{V}$	-	200	-	-	-	-	nA
I_{CBO}	$V_{CB}=200\text{V}$	-	-	-	200	-	-	nA
I_{CBO}	$V_{CB}=250\text{V}$	-	-	-	-	-	200	nA
I_{EBO}	$V_{EB}=5.0\text{V}$	-	100	-	100	-	100	nA
BV_{CB0}	$I_C=100\mu\text{A}$	250	-	300	-	350	-	V
BV_{CEO}	$I_C=1.0\text{mA}$	250	-	300	-	350	-	V
BV_{EBO}	$I_E=100\mu\text{A}$	6.0	-	6.0	-	6.0	-	V
$V_{CE(SAT)}$	$I_C=30\text{mA}, I_B=3.0\text{mA}$	-	0.6	-	0.6	-	0.6	V
$V_{CE(SAT)}$	$I_C=50\text{mA}, I_B=5.0\text{mA}$	-	1.5	-	1.5	-	1.5	V
$V_{BE(ON)}$	$V_{CE}=10\text{V}, I_C=30\text{mA}$	-	0.85	-	0.85	-	0.85	V
h_{FE}	$V_{CE}=10\text{V}, I_C=1.0\text{mA}$	25	-	25	-	25	-	
h_{FE}	$V_{CE}=10\text{V}, I_C=30\text{mA}$	40	180	40	180	40	180	
f_T	$V_{CE}=20\text{V}, I_C=10\text{mA}, f=20\text{MHz}$	45	200	45	200	45	200	MHz
C_{ob}	$V_{CB}=20\text{V}, I_E=0, f=1.0\text{MHz}$	-	3.0	-	3.0	-	3.0	pF

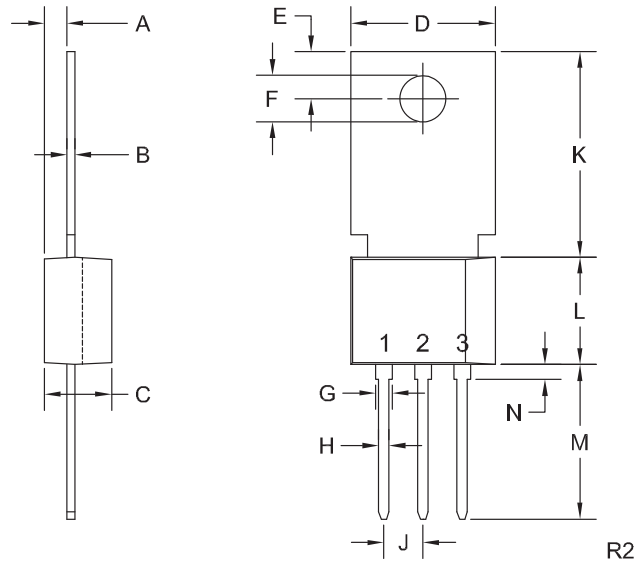
R1 (23-January 2012)

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TO-202 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) Emitter
 - 2) Base
 - 3) Collector
- Tab is common to pin 3

MARKING:

FULL PART NUMBER

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.055	0.071	1.40	1.80
B	0.016	0.024	0.40	0.60
C	0.173	0.181	4.40	4.60
D	0.374	0.413	9.50	10.5
E	0.118	0.154	3.00	3.90
F (DIA)	0.124	0.150	3.15	3.80
G	0.035	0.055	0.90	1.40
H	0.023	0.031	0.59	0.80
J	0.094	0.106	2.39	2.69
K	0.459	0.559	11.66	14.21
L	0.280	0.346	7.12	8.80
M	0.406	0.531	10.3	13.5
N	0.024	0.059	0.60	1.50

TO-202 (REV: R2)

R1 (23-January 2012)